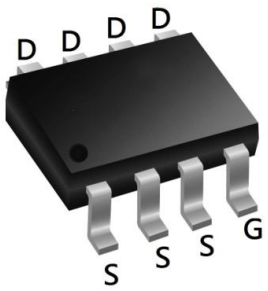
HY12P03

P-Ch 30V Fast Switching MOSFETs

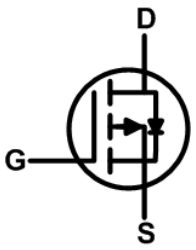
Product Summary

BVDSS	RDSON	ID
-30V	8mΩ	-18A



SOP8

- 100% EAS Guaranteed
- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology



Absolute Maximum Ratings (T_A= 25°C, unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source voltage		V_{DS}	-30	V
Gate-Source voltage		V_{GS}	±20	V
Continuous Drain Current	T_A=25°C	I_D	-18	A
	T_A=100°C		-8.8	
Pulsed Drain Current[1]		I_{DM}	-53	A
Single Pulse Avalanche Energy[2]		EAS	80	mJ
Total Power Dissipation	T_A=25°C	P_D	3	W
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction-to-Ambient[3]	$R_{\theta JA}$	41.6	°C/W

Electrical Characteristics (T_J = 25°C, unless otherwise noted)

Parameter		Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics							
Drain-Source Breakdown Voltage		$V_{(BR)DSS}$	V_{GS} = 0V, I_D = -250μA	-30	-	-	V
Gate-body Leakage current		I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V	-	-	±100	nA
Zero Gate Voltage Drain Current	T_J=25°C	I_{DSS}	V_{DS} = -30V, V_{GS} = 0V	-	-	-1	μA
	T_J=100°C			-	-	-100	
Gate-Threshold Voltage		$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250μA	-1.0	-	-2.5	V
Drain-Source On-Resistance[4]		$R_{DS(on)}$	V_{GS} = -10V, I_D = -12A	-	8	10.4	mΩ
			V_{GS} = -4.5V, I_D = -10A	-	11	14	
Forward Transconductance[4]		g_{fs}	V_{DS} = -10V, I_D = -10A	-	50	-	S
Dynamic Characteristics[5]							
Input Capacitance		C_{iss}	V_{DS} = -15V, V_{GS} =0V, f =1MHz	-	3100	-	pF
Output Capacitance		C_{oss}		-	430	-	
Reverse Transfer Capacitance		C_{rss}		-	358	-	
Gate Resistance		R_g	f=1MHz	-	9.5	-	Ω
Switching Characteristics[5]							
Total Gate Charge		Q_g	V_{GS} = -10V, V_{DS} = -15V I_D= -12A	-	35	-	nC
Gate-Source Charge		Q_{gs}		-	9.9	-	
Gate-Drain Charge		Q_{gd}		-	10.5	-	
Turn-On Delay Time		$t_{d(on)}$	V_{GS} =-10V, V_{DD} = -15V R_G = 3Ω, I_D= -12A	-	10.8	-	ns
Rise Time		t_r		-	13.2	-	
Turn-Off Delay Time		$t_{d(off)}$		-	73	-	
Fall Time		t_f		-	35	-	
Reverse Recovery Time		t_{rr}	I_F = -12A, dI_F/dt = 100A/μs	-	25	-	ns
Reverse Recovery Charge		Q_{rr}		-	10	-	nC
Drain-source body diode Characteristics							
Diode Forward Voltage[4]		V_{SD}	I_S = -1A, V_{GS} = 0V	-	-	-1.2	V
Continuous Source Current	T_A=25°C	I_S	-	-	-	-14	A

Typical Characteristics

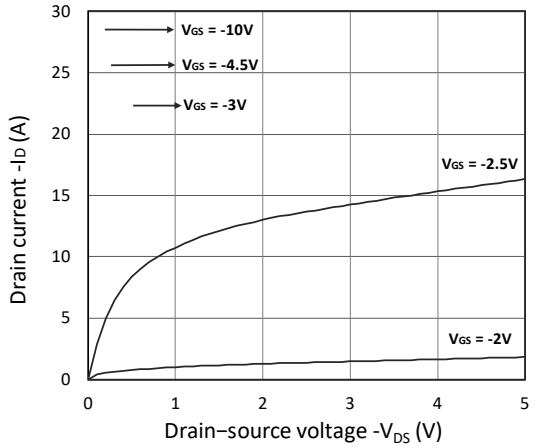


Figure 1. Output Characteristics

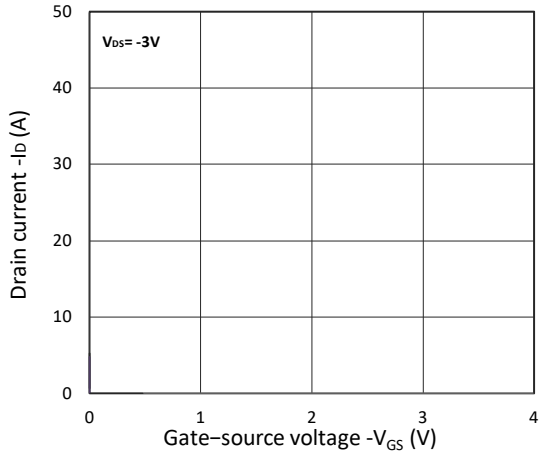


Figure 2. Transfer Characteristics

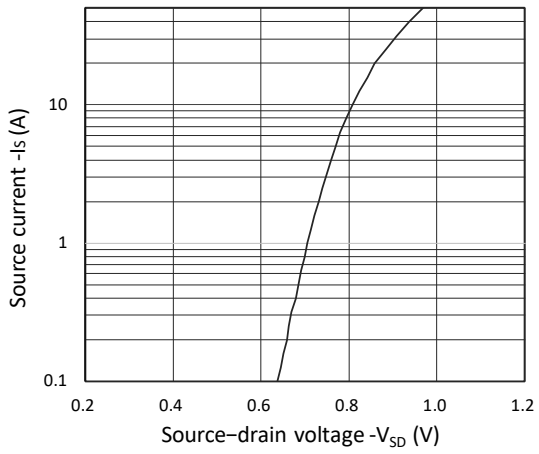


Figure 3. Forward Characteristics of Reverse

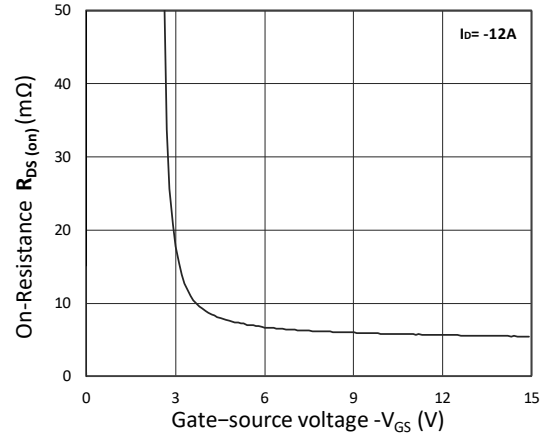


Figure 4. $R_{DS(ON)}$ vs. V_{GS}

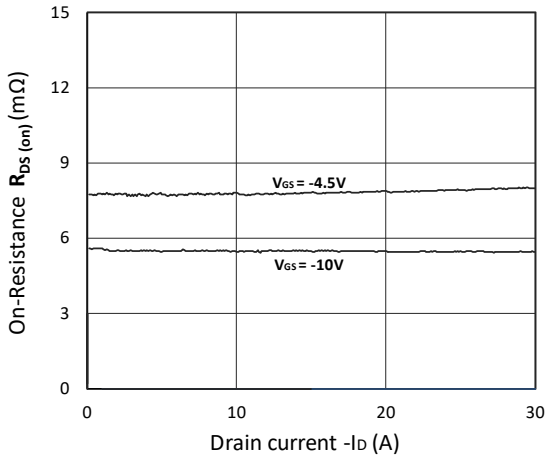


Figure 5. $R_{DS(ON)}$ vs. I_D

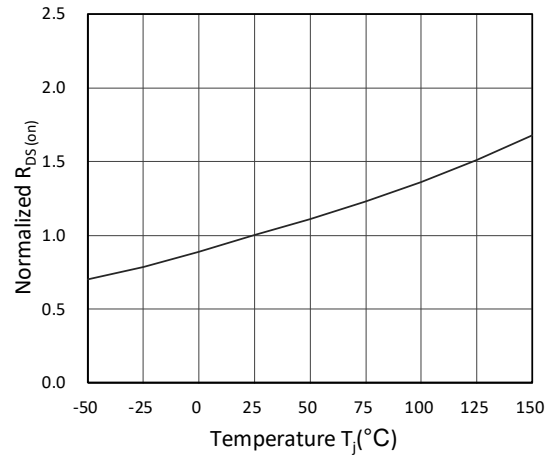


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

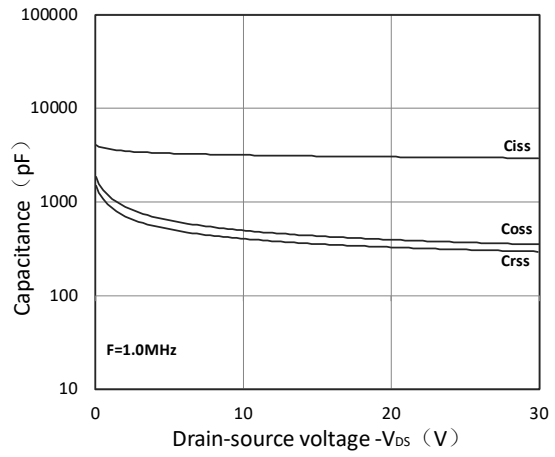


Figure 7. Capacitance Characteristics

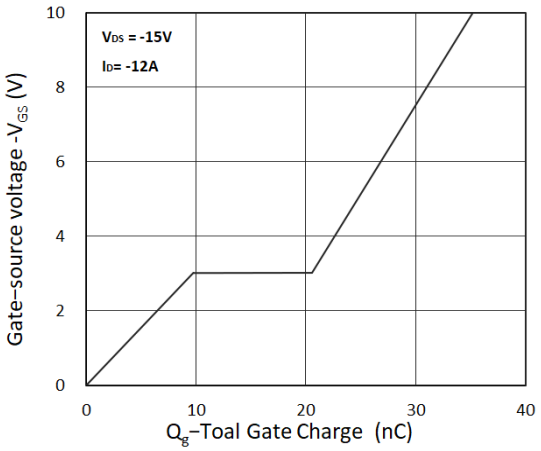


Figure 8. Gate Charge Characteristics

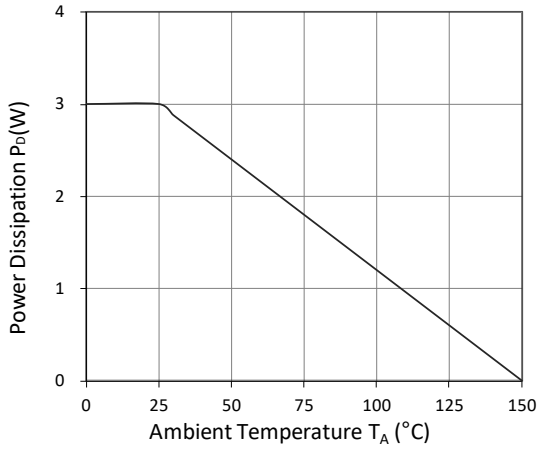


Figure 9. Power Dissipation

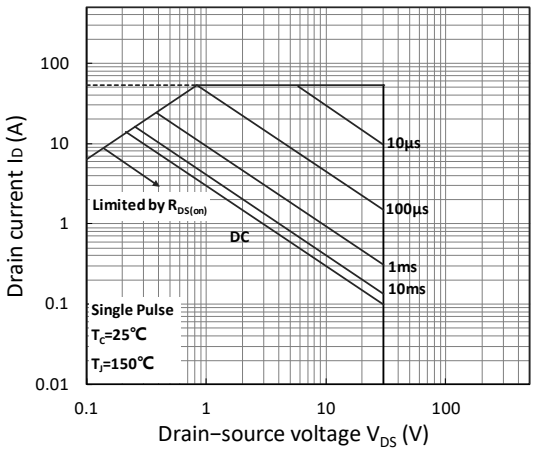


Figure10. Safe Operating Area

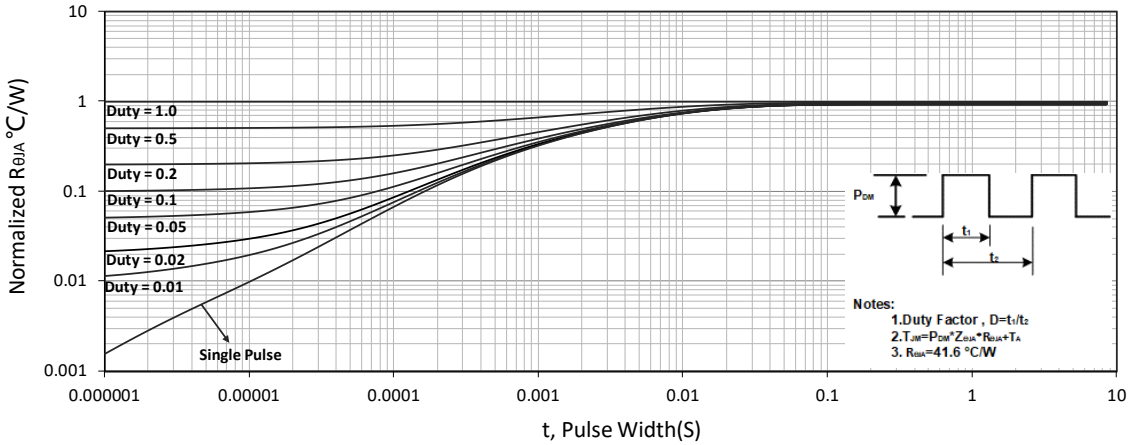


Figure 11. Normalized Maximum Transient Thermal Impedance

Test Circuit

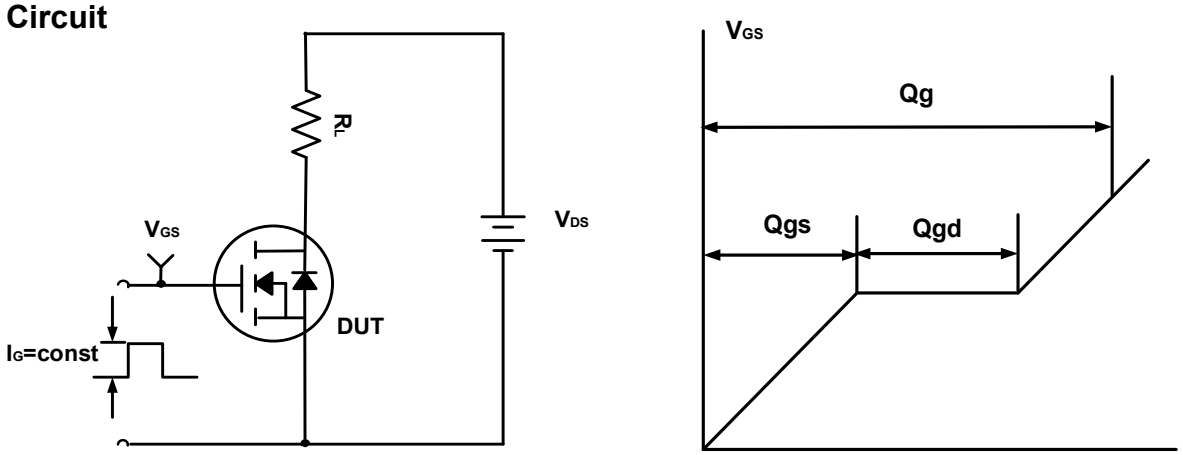


Figure A. Gate Charge Test Circuit & Waveforms

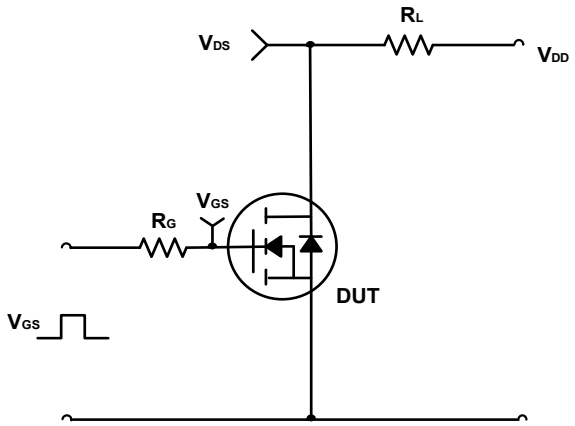


Figure B. Switching Test Circuit & Waveforms

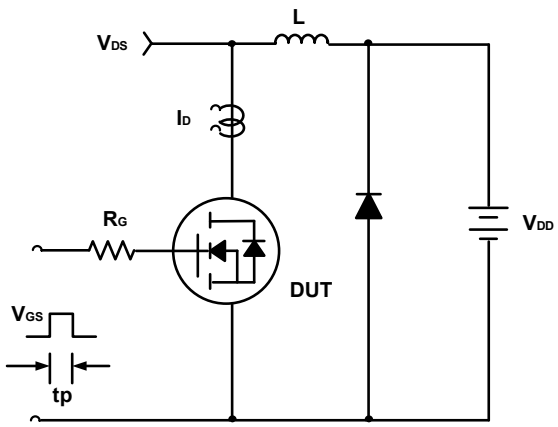
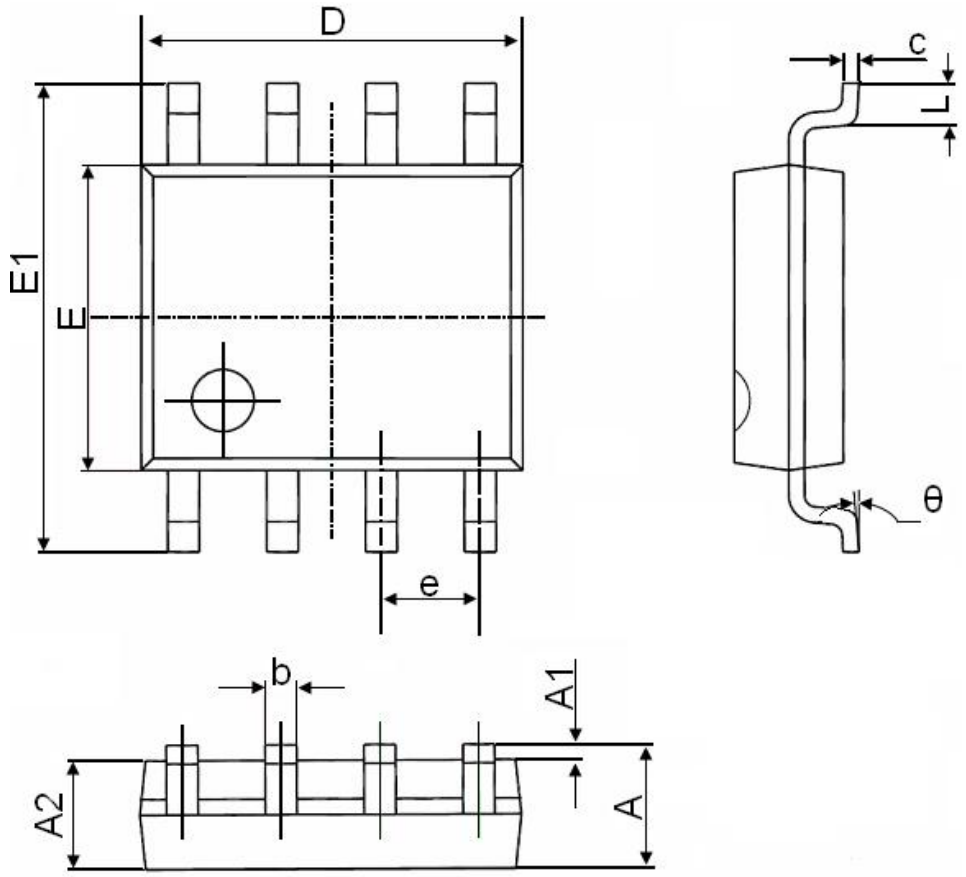


Figure C. Unclamped Inductive Switching Circuit & Waveforms

SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°